

**Maximum Ratings** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	20	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Drain Current (Note 5)	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	540	mA
		T <sub>A</sub> = +85°C		390	
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	1.5	A

**Thermal Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_D$	200	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	$BV_{DS}$	20	—	—	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	1	$\mu A$	$V_{DS} = 16V, V_{GS} = 0V$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 1$	$\mu A$	$V_{GS} = \pm 4.5V, V_{DS} = 0V$
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	0.5	—	1.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	0.4	0.55	$\Omega$	$V_{GS} = 4.5V, I_D = 540mA$
			0.5	0.70		$V_{GS} = 2.5V, I_D = 500mA$
			0.7	0.9		$V_{GS} = 1.8V, I_D = 350mA$
			—	—		$V_{GS} = 1.8V, I_D = 350mA$
Forward Transfer Admittance	$ Y_{fs} $	200	—	—	mS	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage (Note 7)	$V_{SD}$	0.5	—	1.4	V	$V_{GS} = 0V, I_S = 115mA$
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Input Capacitance	$C_{iss}$	—	36	150	pF	$V_{DS} = 16V, V_{GS} = 0V$ $f = 1.0MHz$
Output Capacitance	$C_{oss}$	—	5.7	25	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	4.2	20	pF	
Total Gate Charge ( $V_{GS} = 4.5V$ )	$Q_g$	—	0.53	—	nC	$V_{DS} = 10V, I_D = 250mA$
Total Gate Charge ( $V_{GS} = 8.0V$ )	$Q_g$	—	0.95	—		
Gate-Source Charge	$Q_{gs}$	—	0.08	—		
Gate-Drain Charge	$Q_{gd}$	—	0.07	—		
Turn-On Delay Time	$t_{D(ON)}$	—	4.1	—	ns	$V_{DD} = 10V, R_L = 47\Omega,$ $V_{GEN} = 4.5V, R_{GEN} = 10\Omega$
Turn-On Rise Time	$t_r$	—	7.3	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	13.8	—	ns	
Turn-Off Fall Time	$t_f$	—	10.5	—	ns	

Notes: 5. Device mounted on FR-4 PCB.  
6. Pulse width  $\leq 10\mu s$ , Duty Cycle  $\leq 1\%$ .  
7. Short duration pulse test used to minimize self-heating effect.

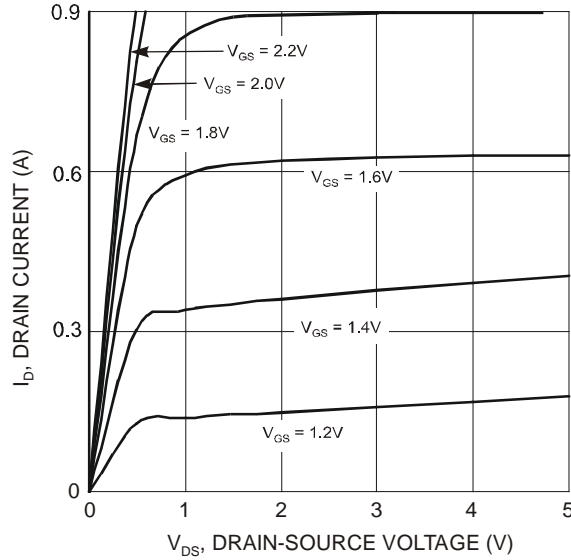


Fig. 1 Typical Output Characteristics

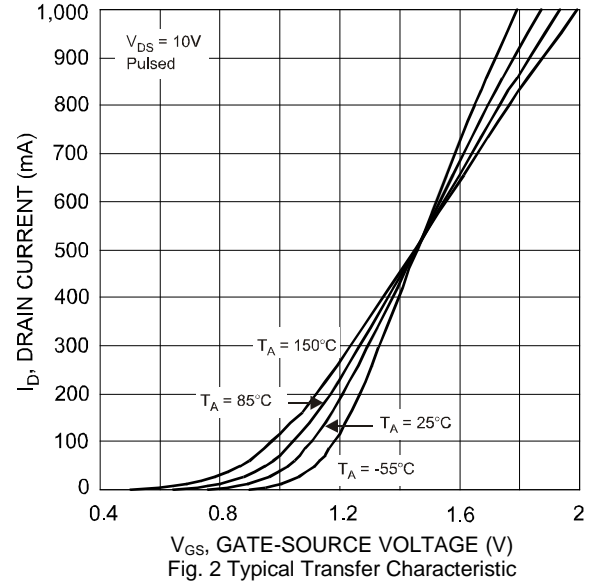


Fig. 2 Typical Transfer Characteristic

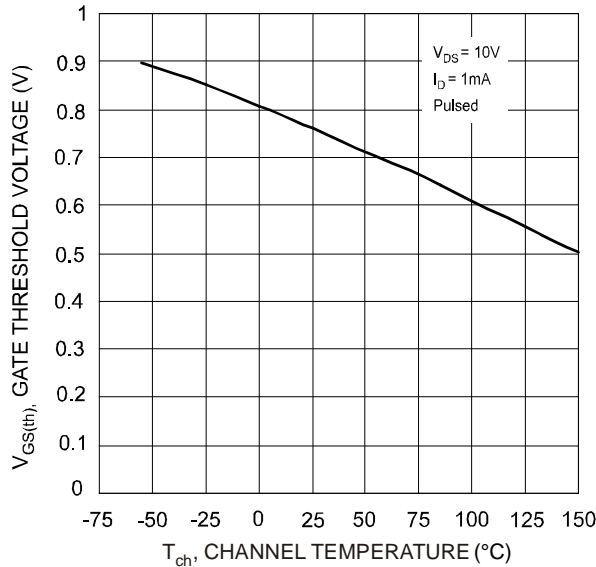


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

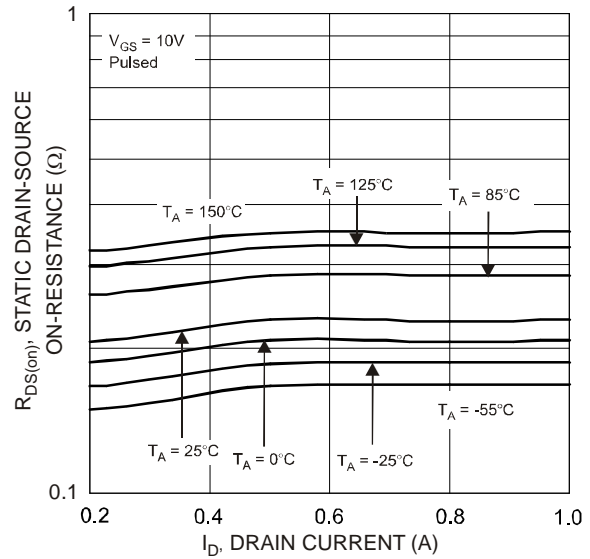


Fig. 4 Static Drain-Source On-Resistance Vs. Drain Current

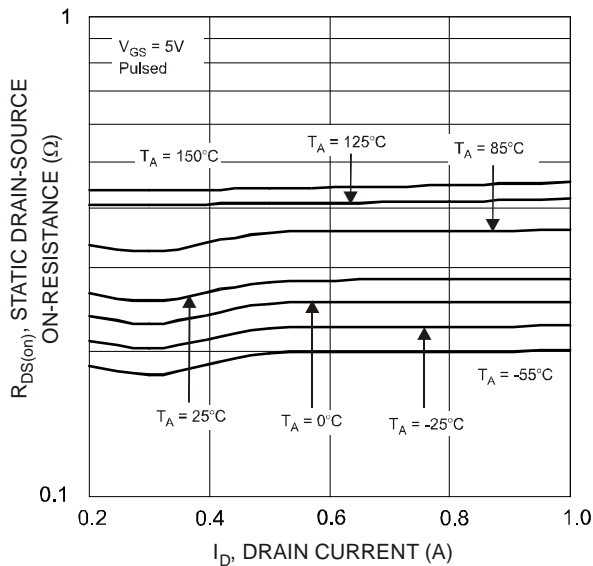


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

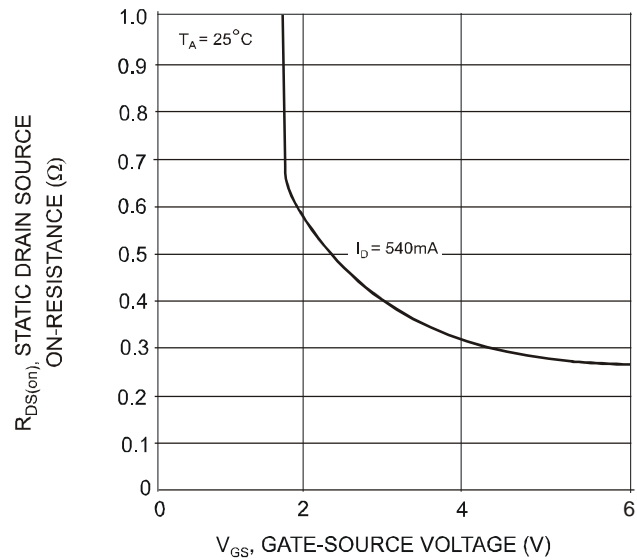


Fig. 6 Static Drain-Source, On-Resistance vs. Gate-Source Voltage

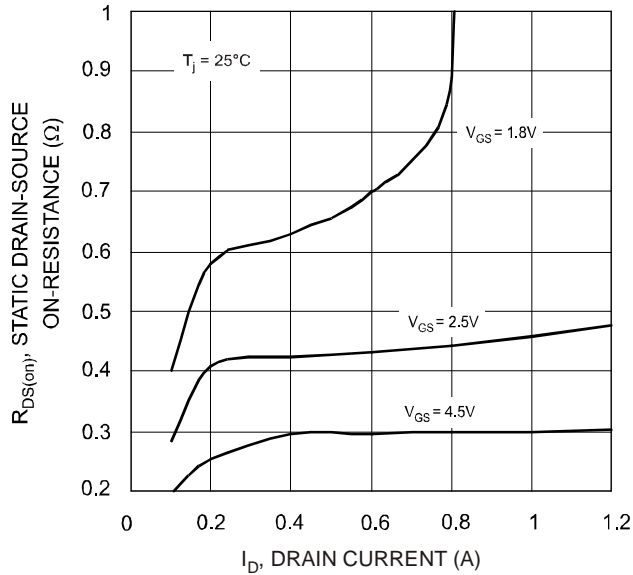


Fig. 7 On-Resistance vs. Drain Current and Gate Voltage

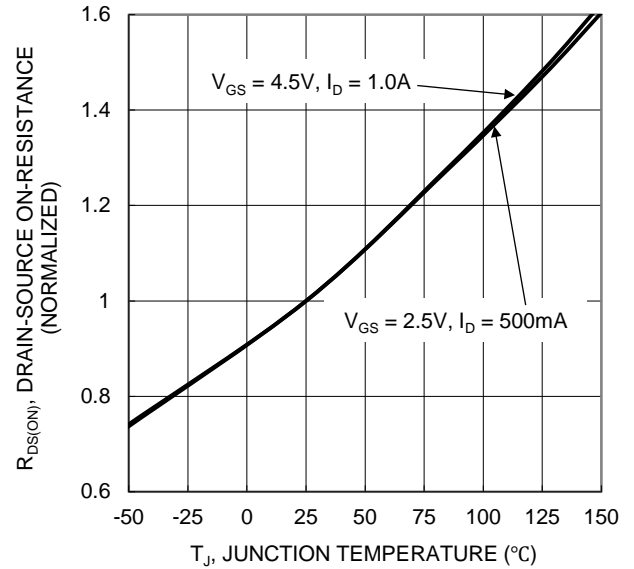


Fig. 8 On-Resistance Variation with Temperature

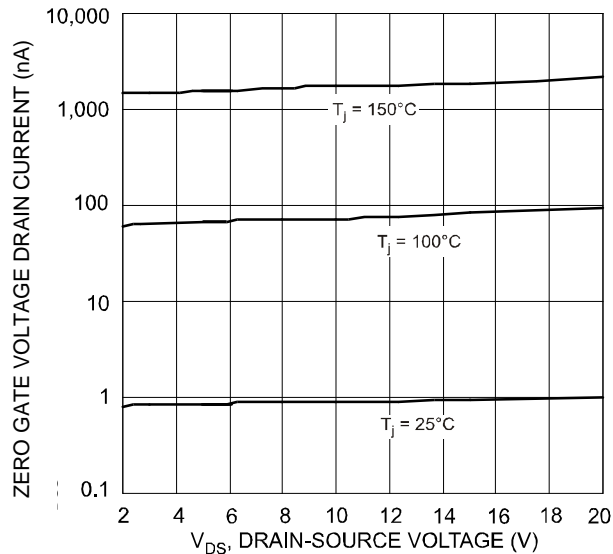


Fig. 9 Drain Source Leakage Current vs. Voltage

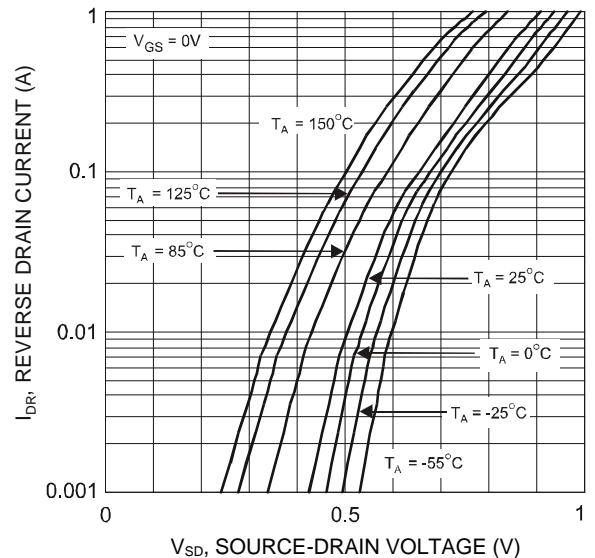


Fig. 10 Reverse Drain Current vs. Source-Drain Voltage

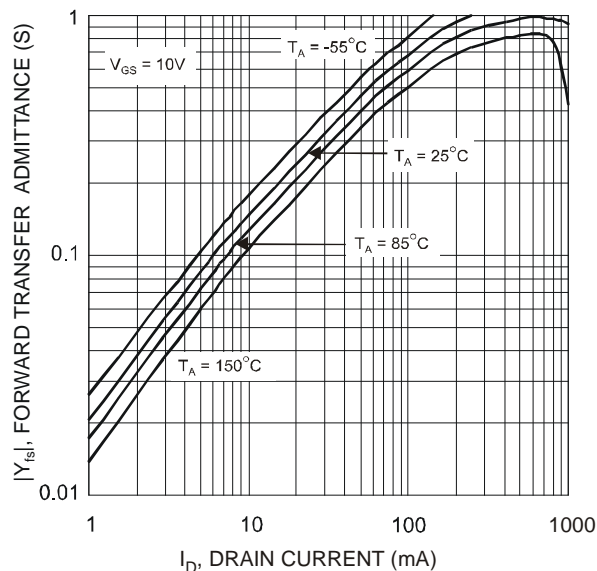


Fig. 11 Forward Transfer Admittance vs. Drain Current

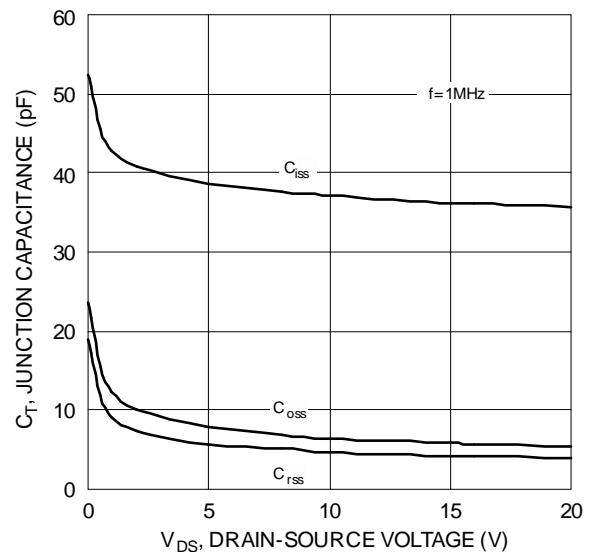
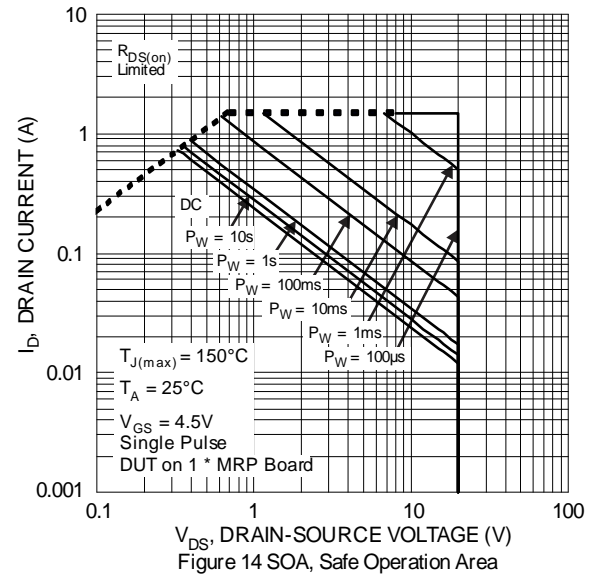
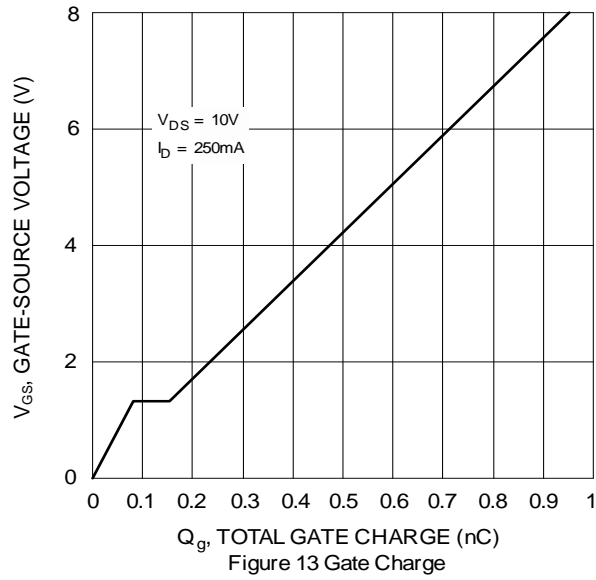
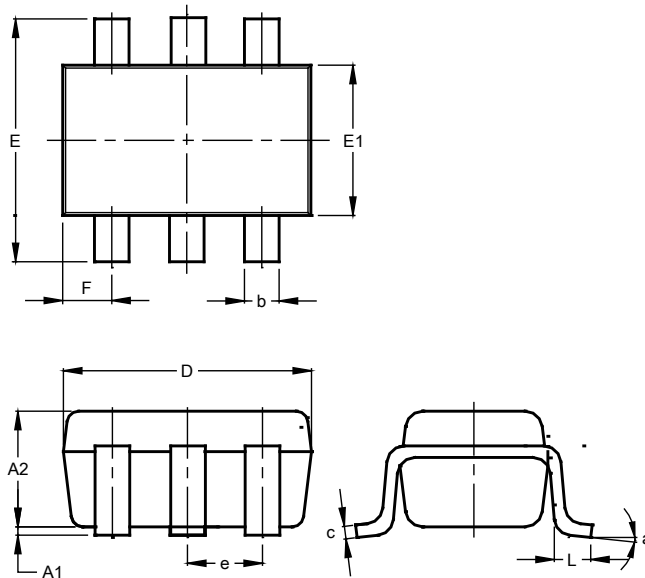


Figure 12 Typical Junction Capacitance



## Package Outline Dimensions

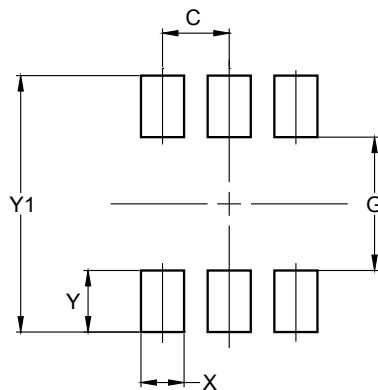
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



SOT363			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	1.00
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

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